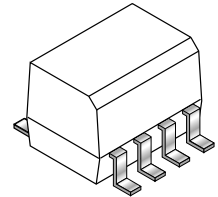


**MOCD217-M**

**DESCRIPTION**

The MOCD217-M device consists of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline plastic package. It is ideally suited for high density applications and eliminates the need for through-the-board mounting.

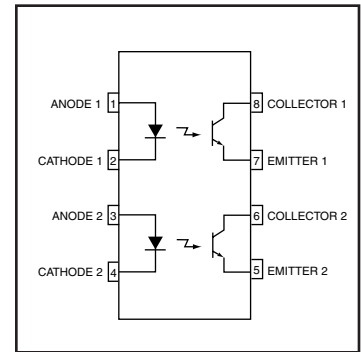


**FEATURES**

- U.L. Recognized (File #E90700, Volume 2)
- VDE Recognized (File #136616) (add option "V" for VDE approval, i.e, MOCD217V-M)
- Low Input Current (Specified @ 1 mA)
- Minimum  $BV_{CEO}$  of 30 Volts Guaranteed
- Convenient Plastic SOIC-8 Surface Mountable Package Style
- Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input-Output Isolation of 2500  $V_{AC(rms)}$  Guaranteed

**APPLICATIONS**

- Interfacing and coupling systems of different potentials and impedances
- General purpose switching circuits
- Monitor and detection circuits



<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^\circ\text{C}$ Unless otherwise specified)			
Rating	Symbol	Value	Unit
<b>EMITTER</b>			
Forward Current - Continuous	$I_F$	60	mA
Forward Current - Peak (PW = 100 $\mu\text{s}$ , 120 pps)	$I_F$ (pk)	1.0	A
Reverse Voltage	$V_R$	6.0	V
LED Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	90 0.8	mW mW/ $^\circ\text{C}$
<b>DETECTOR</b>			
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Collector Voltage	$V_{ECO}$	7.0	V
Collector Current-Continuous	$I_C$	150	mA
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	150 1.76	mW mW/ $^\circ\text{C}$
<b>TOTAL DEVICE</b>			
Input-Output Isolation Voltage <sup>(1,2,3)</sup> (f = 60 Hz, 1 min. Duration)	$V_{ISO}$	2500	Vac(rms)
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	250 2.94	mW mW/ $^\circ\text{C}$
Ambient Operating Temperature Range	$T_A$	-40 to +100	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40 to +125	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise specified)

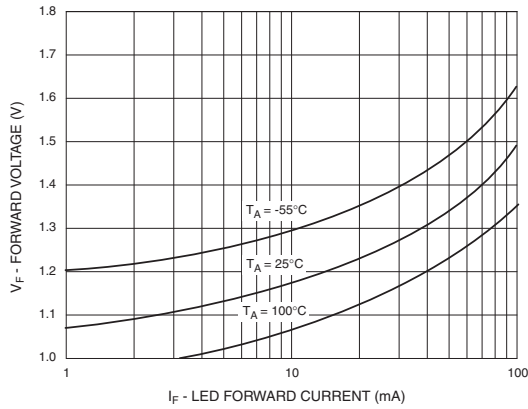
Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
<b>EMITTER</b>						
Input Forward Voltage	$I_F = 1.0 \text{ mA}$	$V_F$	—	1.05	1.3	V
Reverse Leakage Current	$V_R = 6.0 \text{ V}$	$I_R$	—	0.1	100	$\mu\text{A}$
Capacitance		C	—	18	—	pF
<b>DETECTOR</b>						
Collector-Emitter Dark Current	$V_{CE} = 10 \text{ V}, T_A = 25^\circ\text{C}$	$I_{CEO1}$	—	1.0	50	nA
	$V_{CE} = 10 \text{ V}, T_A = 100^\circ\text{C}$	$I_{CEO2}$	—	1.0	—	$\mu\text{A}$
Collector-Emitter Breakdown Voltage	$I_C = 100 \mu\text{A}$	$BV_{CEO}$	30	90	—	V
Emitter-Collector Breakdown Voltage	$I_E = 100 \mu\text{A}$	$BV_{ECO}$	7.0	7.8	—	V
Collector-Emitter Capacitance	$f = 1.0 \text{ MHz}, V_{CE} = 0 \text{ V}$	$C_{CE}$	—	7.0	—	pF
<b>COUPLED</b>						
Output Collector Current <sup>(4)</sup>	$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}$	CTR	100	130	—	%
Collector-Emitter Saturation Voltage	$I_C = 100 \mu\text{A}, I_F = 1.0 \text{ mA}$	$V_{CE(sat)}$	—	0.35	0.4	V
Turn-On Time	$I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$ (fig 6.)	$t_{on}$	—	7.5	—	$\mu\text{s}$
Turn-Off Time	$I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$ (fig 6.)	$t_{off}$	—	5.7	—	$\mu\text{s}$
Rise Time	$I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$ (fig 6.)	$t_r$	—	3.2	—	$\mu\text{s}$
Fall Time	$I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$ (fig 6.)	$t_f$	—	4.7	—	$\mu\text{s}$
Isolation Surge Voltage <sup>(1,2,3)</sup>	$f = 60 \text{ Hz}, t = 1 \text{ min.}$	$V_{ISO}$	2500	—	—	Vac(rms)
Isolation Resistance <sup>(2)</sup>	$V_{I-O} = 500 \text{ V}$	$R_{ISO}$	$10^{11}$	—	—	$\Omega$
Isolation Capacitance <sup>(2)</sup>	$V_{I-O} = 0 \text{ V}, f = 1 \text{ MHz}$	$C_{ISO}$	—	0.2	—	pF

\*\* Typical values at  $T_A = 25^\circ\text{C}$

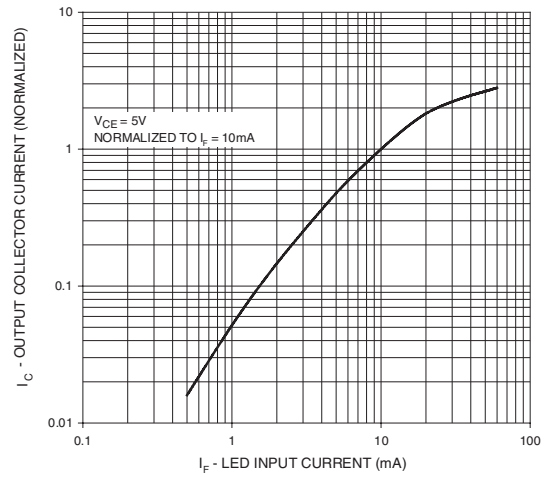
**NOTE:**

1. Input-Output Isolation Voltage,  $V_{ISO}$ , is an internal device dielectric breakdown rating.
2. For this test, Pins 1, 2, 3 and 4 are common and Pins 5, 6, 7 and 8 are common.
3.  $V_{ISO}$  rating of  $2500 V_{AC(rms)}$  for  $t = 1 \text{ min.}$  is equivalent to a rating of  $3,000 V_{AC(rms)}$  for  $t = 1 \text{ sec.}$
4. Current Transfer Ratio (CTR) =  $I_C/I_F \times 100\%$ .

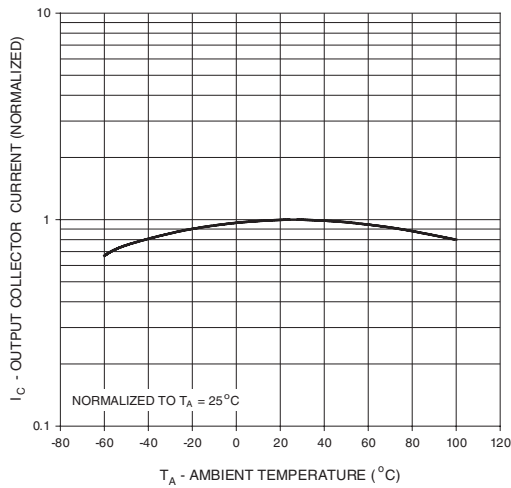
**Fig. 1 LED Forward Voltage vs. Forward Current**



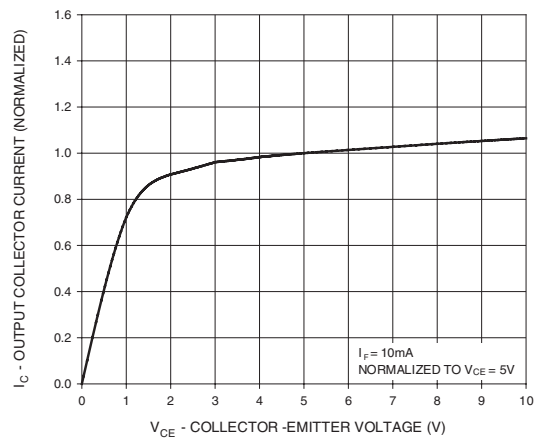
**Fig. 2 Output Current vs. Input Current**



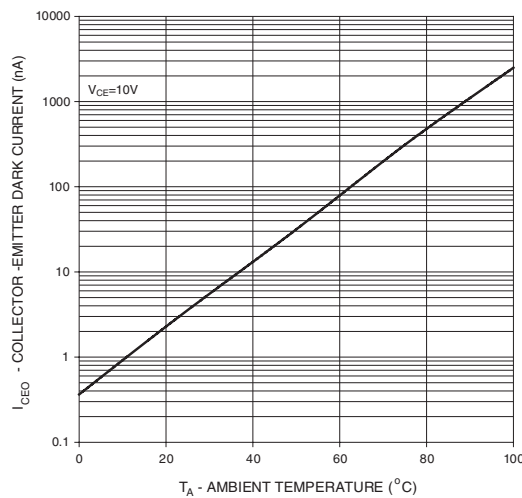
**Fig. 3 Output Current vs. Ambient Temperature**

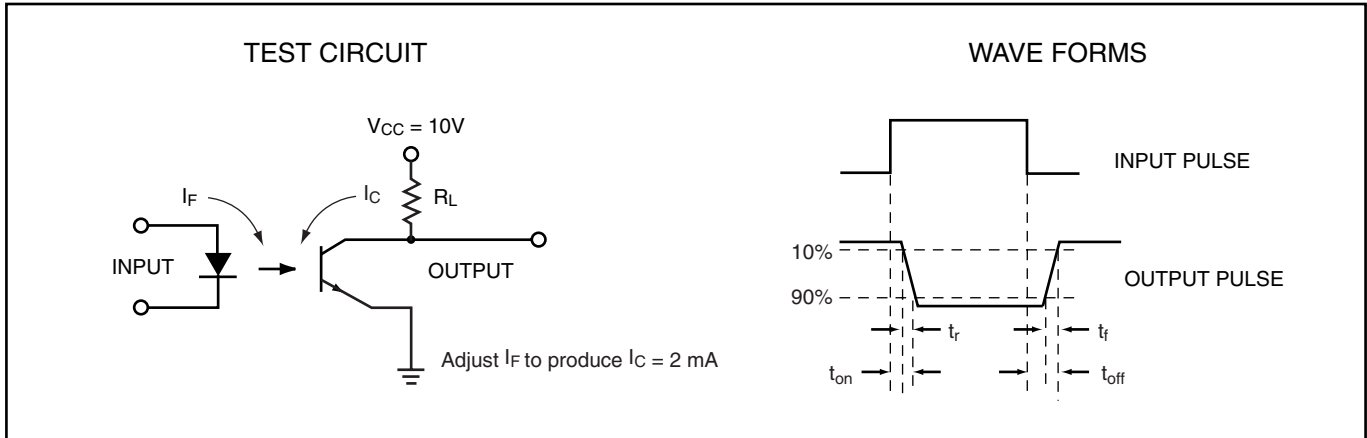


**Fig. 4 Output Current vs. Collector - Emitter Voltage**



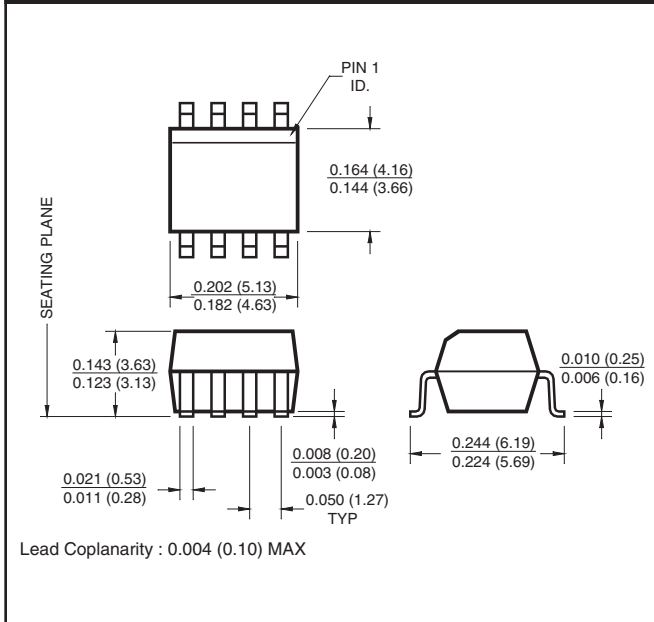
**Fig. 5 Dark Current vs. Ambient Temperature**



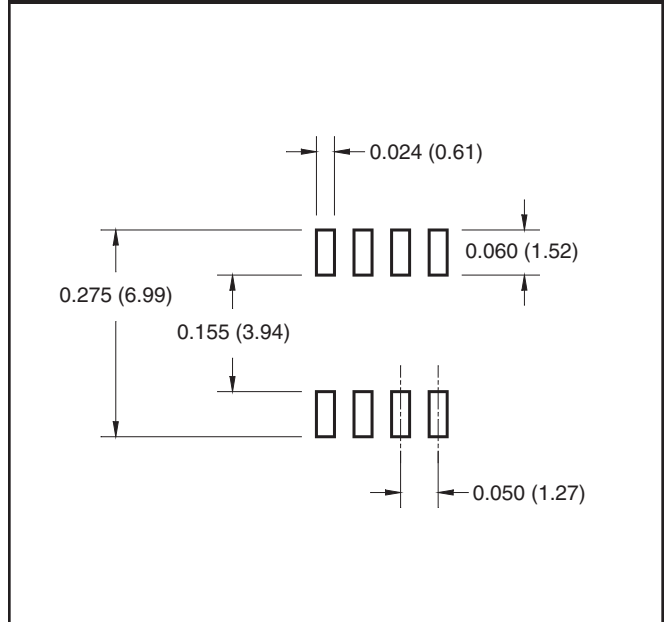


**Figure 6. Switching Time Test Circuit and Waveforms**

**Package Dimensions (Surface Mount)**



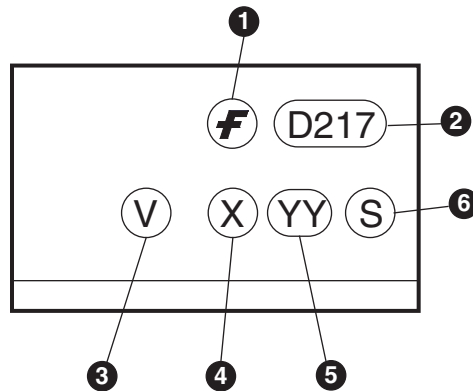
**8-Pin Small Outline**



**ORDERING INFORMATION**

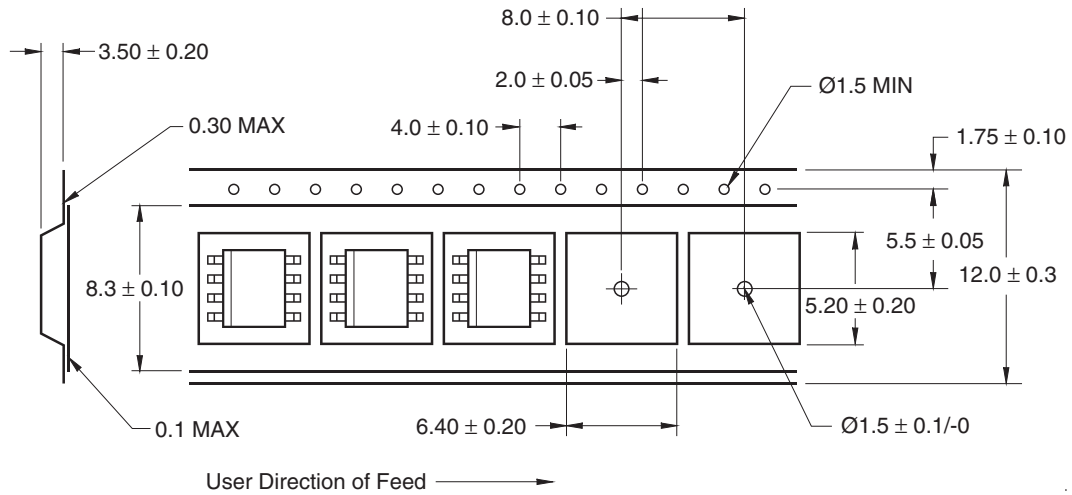
Option	Order Entry Identifier	Description
V	V	VDE 0884
R1	R1	Tape and reel (500 units per reel)
R1V	R1V	VDE 0884, Tape and reel (500 units per reel)
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

**MARKING INFORMATION**

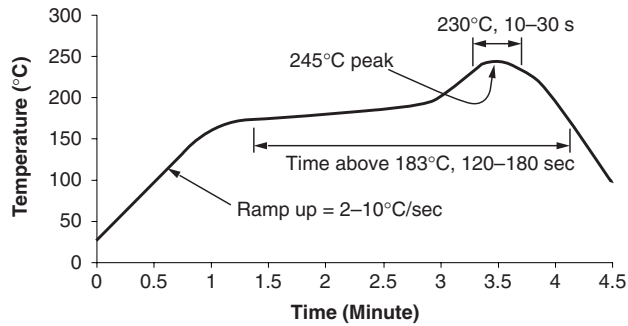


Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '3'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

**Carrier Tape Specifications**



**Reflow Profile**



- Peak reflow temperature: 245°C (package surface temperature)
- Time of temperature higher than 183°C for 120-180 seconds
- One time soldering reflow is recommended

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.